

X00135

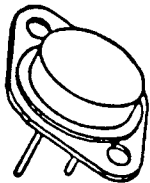
SFT1010 SFT1012 SFT1014
100 AMP
HIGH ENERGY NPN TRANSISTORS
V_{CEO} 100, 120, 140 VOLTS



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CASE STYLE R

TO-3 WITH .060 PINS



FEATURES

- BVCBO 250 VOLTS MIN
- 300 WATTS POWER DISSIPATION
- EXCELLENT SOA CURVE
- Es/b OF 400mJ
- GAIN OF OVER 5 AT 100 AMPS
- HIGH REL CONSTRUCTION INCLUDING GOLD EUTECTIC DIE MOUNTING, ALUMINUM WIRING
- PLANAR CHIP CONSTRUCTION WITH LOW LEAKAGE AND VERY FAST SWITCHING

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage SFT1010 SFT1012 SFT1014	V _{CEO}	100 120 140	Volts
Collector - Base Voltage	V _{CBO}	250	Volts
Emitter - Base Voltage	V _{EBO}	8	Volts
Collector Current	I _C	100	Amps
Base Current	I _B	35	Amps
Total Device Dissipation @ TC = 50 °C Derate above 50 °C	P _D	300 2	Watts W/°C
Operating and Storage Temperature	T _j , T _{stg}	-65 to 200	°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Value	Unit
Thermal Resistance, Junction to Case	R _{θJC}	0.5	°C/W

ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Min.	Max.	Unit
Collector - Emitter Breakdown Voltage* (I _C = 200 mA dc) SFT1010 SFT1012 SFT1014	BV _{CEO}	100 120 140		Vdc
Collector - Base Breakdown Voltage (I _C = 100 μA dc)	BV _{CBO}	250		Vdc
Emitter - Base Breakdown Voltage (I _E = 100 μA dc)	BV _{EBO}	8		Vdc

NOTE: All specifications subject to change without notice.

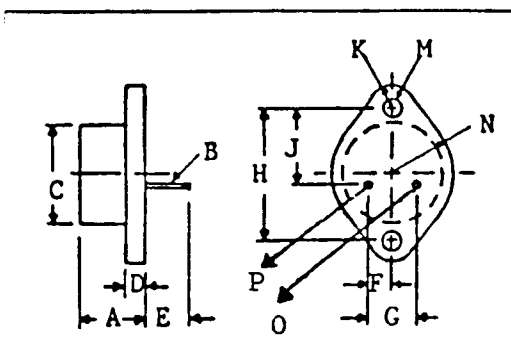
ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Min.	Max.	Unit
Collector Cutoff Current ($V_{CB} = 250 \text{ Vdc}$)	I_{CBO}		10	μA
Emitter Cutoff Current ($V_{EB} = 7 \text{ Vdc}$)	I_{EBO}		10	μA
DC Current Gain* ($I_C = 10 \text{ A}$ dc, $V_{CE} = 2 \text{ Vdc}$) ($I_C = 50 \text{ A}$ dc, $V_{CE} = 5 \text{ Vdc}$) ($I_C = 100 \text{ A}$ dc, $V_{CE} = 5 \text{ Vdc}$)	h_{FE}	40 30 7		
Collector - Emitter Saturation Voltage* ($I_C = 50 \text{ A}$ dc, $I_B = 5 \text{ A}$ dc) ($I_C = 100 \text{ A}$ dc, $I_B = 10 \text{ A}$ dc)	$V_{CE(SAT)}$		2 4	Vdc
Base - Emitter Saturation Voltage* ($I_C = 100 \text{ A}$ dc, $I_B = 10 \text{ A}$ dc)	$V_{BE(SAT)}$		2.5	Vdc
Current - Gain - Bandwidth Product ($I_C = 1 \text{ A}$ dc, $V_{CE} = 10 \text{ Vdc}$, $f = 10 \text{ MHz}$)	f_T	35		MHz
Output Capacitance ($V_{CB} = 10 \text{ Vdc}$, $I_E = 0.1 \text{ A}$, $f = 1 \text{ MHz}$)	C_{ob}		600	pf
RBSOA ($I_B = 1 \text{ A}$ dc, $R_{B1} = R_{B2} = 20 \text{ ohms}$, $V_{BE(off)} = 2.0 \text{ Vdc}$, $L = 1.0 \text{ mH}$)	$E_{s/b}$	400		mJ
FBSOA ($V_{CE} = 20 \text{ Vdc}$, $I_C = 15 \text{ A}$ dc) ($V_{CE} = 100 \text{ Vdc}$, $I_C = 0.4 \text{ A}$ dc)	$I_{s/b}$	1 1		sec
ON TIME ($V_{CC} = 60 \text{ Vdc}$, $I_C = 10 \text{ A}$ dc, $I_{B1} = I_{B2} = 1.0 \text{ A}$ dc)	t_{on}		800	ns
Storage Time	t_s		1500	ns
Fall Time	t_f		400	ns

Pulse Test: Pulse width = 300 μs , Duty Cycle = 2%

PHYSICAL DIMENSIONS

KEY TO DIMENSIONS:



(Inches)

A =	.250 - .450
B =	.057 - .062
C =	.875 MAX.
D =	.135 MAX.
E =	.312 MIN.
F =	.205 - .225
G =	.420 - .440
H =	1.177 - 1.197
J =	.655 - .675
K =	.188 MAX.
M =	.151 - .161
N =	.525 MAX.
O =	BASE
P =	EMITTER

SSDI

SOLID STATE DEVICES, INC.